

	Type	Hits	Search Text
1	BRS	2665	257/\$.CCLLS. and (passivation adj layer or passive adj layer)
2	BRS	2612	257/\$.CCLLS. and (passivation adj layer) or (passive adj layer)
3	BRS	0	257/\$.CCLLS. and (passivation adj layer or passive adj layer) and (SiGe with heterojunction with bipolar with transistor)
4	BRS	2	257/\$.CCLLS. and ((passivation adj layer) or (passive adj layer)) and (SiGe) and (heterojunction with bipolar with transistor)
5	BRS	1	257/\$.CCLLS. and ((passivation adj layer) or (passive adj layer)) and (SiGe) and (heterojunction with bipolar with transistor) and (nitride or oxide or oxynitride)
6	BFS	1	257/\$.CCLLS. and ((passivation adj layer) or (passive adj layer)) and (SiGe) and (heterojunction with bipolar with transistor) and (nitride or oxide or oxynitride) and emitter
7	BFS	1	257/\$.CCLLS. and ((passivation adj layer) or (passive adj layer)) and (SiGe) and (heterojunction with bipolar with transistor) and (nitride and oxide and oxynitride) and emitter
8	BRS	1	257/197.CCLLS. and (SiGe) and (heterojunction with bipolar with transistor) and (nitride and oxide and oxynitride) and (emitter)
9	BFS	38	257/197.CCLLS. and (SiGe) and (heterojunction with bipolar with transistor) and (emitter)
10	BRS	24	438/312,348,320,314,364.CCLLS. and (SiGe) and (heterojunction with bipolar with transistor) and (emitter)
11	BRS	0	438/312,348,320,314,364.CCLLS. and (SiGe) and (heterojunction with bipolar with transistor) and (emitter) and nitride and oxide and oxynitride
12	BRS	1	438/312,348,320,314,364.CCLLS. and (SiGe) and (emitter) and nitride and oxide and oxynitride

	DBs	Time Stamp	Comments	Error Definition
1	USPAT; US-PGPUB	2001/12/13 11:43		
2	USPAT; EPO; JPO; DERWENT	2001/12/13 11:44		
3	USPAT; EPO; JPO; DERWENT	2001/12/13 11:46		
4	USPAT; EPO; JPO; DERWENT	2001/12/13 13:16		
5	USPAT; EPO; JPO; DERWENT	2001/12/13 11:52		
6	USPAT; EPO; JPO; DERWENT	2001/12/13 12:26		
7	USPAT; EPO; JPO; DERWENT	2001/12/13 12:32		
8	USPAT; EPO; JPO; DERWENT	2001/12/13 12:33		
9	USPAT; EPO; JPO; DERWENT	2001/12/13 12:52		
10	USPAT; EPO; JPO; DERWENT	2001/12/13 12:53		
11	USPAT; EPO; JPO; DERWENT	2001/12/13 12:54		
12	USPAT; EPO; JPO; DERWENT	2001/12/13 12:59		

	Errors
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9	0
10	0
11	0
12	0

	Type	Hits	Search Text
13	BRS	1	438,312,348,320,314,364.COLS. and SiGe and emitter and nitride and oxide and oxynitride and heterojunction
14	IS&F	1	"6169007".PN.
15	BRS	4	257/S.COLS. and (collector) and (subcollector) and (isolation or isolated) and (SiGe) and (polycrystalline with (si or silicon) and (heterojunction with bipolar with transistor) and (emitter)
16	IS&F	1	("6169007").PN.
17	IS&F	1	("5834800").PN.
18	IS&F	1	("5620907").PN.
19	IS&F	2	("6169007").PN.
20	IS&F	1	("5620907").PN.
21	IS&F	2	("6169007").PN.
22	BFS	12	438/S.COLS. and (rapid adj thermal adj chemical adj vapor) and (nitrogen) and "000"
23	BFS	2	"6169007"
24	IS&F	1	("5899511").PN.
25	IS&F	1	("6169007").PN.
26	IS&F	1	("5899511").PN.
27	IS&F	1	("6169007").PN.
28	IS&F	1	("5899511").PN.
29	BRS	495	257/S.cols. and (nitride with oxide with oxynitride)
30	BRS	12	257/S.cols. and (nitride with oxide with oxynitride)

	DBs	Time Stamp	Comments	Error Definition
13	USPAT; EPO; JPO; DERWENT	2001/12/14 10:51		
14	USPAT; US-PGPUB	2001/12/13 13:16		
15	USPAT; EPO; JPO; DERWENT	2001/12/13 14:24		
16	USPAT; US-PGPUB	2001/12/13 14:25		
17	USPAT; US-PGPUB	2001/12/13 14:25		
18	USPAT; US-PGPUB	2001/12/13 14:25		
19	USPAT; EPO; JPO; DERWENT	2001/12/13 16:05		
20	USPAT; US-PGPUB	2001/12/13 16:22		
21	USPAT; EPO; JPO; DERWENT	2001/12/14 08:45		
22	USPAT; EPO; JPO; DERWENT	2001/12/14 10:30		
23	USPAT; EPO; JPO; DERWENT	2001/12/14 10:31		
24	USPAT; US-PGPUB	2001/12/14 10:34		
25	USPAT; US-PGPUB	2001/12/14 10:35		
26	USPAT; US-PGPUB	2001/12/14 10:36		
27	USPAT; US-PGPUB	2001/12/14 10:38		
28	USPAT; US-PGPUB	2001/12/14 10:38		
29	USPAT; EPO; JPO; DERWENT	2001/12/14 12:40		
30	EPO; JPO; DERWENT	2001/12/14 12:40		

	Errors
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